

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 07-245292

(43)Date of publication of application : 19.09.1995

(51)Int.CI.

H01L 21/3065

(21)Application number : 06-033645

(71)Applicant : TOKYO ELECTRON LTD  
TOSHIBA CORP

(22)Date of filing : 03.03.1994

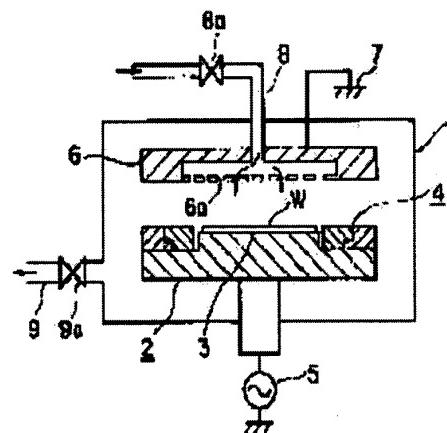
(72)Inventor : HASEGAWA MAKOTO  
KANBARA HIROMITSU  
ISHIKAWA YOSHIO  
IMAMURA YASUO  
AOKI MAKOTO

## (54) PLASMA ETCHING SYSTEM

### (57)Abstract:

**PURPOSE:** To provide a plasma etching system that achieves the improved uniformity in etching rate across the entire surface of a workpiece, and that is capable of easily coping with any change to etching process conditions for such improved uniformity in etching rate.

**CONSTITUTION:** With the plasma etching system a semiconductor wafer is etched as follows: The semiconductor wafer is placed in a vacuum processing vessel 1, and process gas is introduced into the vessel. High-frequency voltage is applied between a lower electrode 2 and an upper electrode 6 to produce plasma, and the wafer is thereby etched. In this plasma etching system, a focus ring 4 placed on the periphery of the workpiece support section 3 of the lower electrode 2, is of composite structure, wherein an exposed tungsten member is placed on the circumference of the focus ring 4.



**LEGAL STATUS**

[Date of request for examination] 16.10.1998

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3257741

[Date of registration] 07.12.2001

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C) 1998,2003 Japan Patent Office